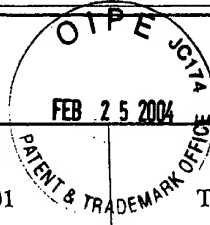


TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
01-27

In Re Application Of: Norio HIRASHITA



RECEIVED
MAR 03 2004

Serial No. NEW	Filing Date APRIL 5, 2001	Examiner TO BE ASSIGNED	Group Art Unit TO BE ASSIGNED
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Title: A STRUCTURE OF A FIELD EFFECT TRANSISTOR HAVING A METALLIC SILICIDE AND
MANUFACTURING METHOD THEREOF

Address to:
Assistant Commissioner for Patents
Washington, D.C. 20231

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:

1. a Final Action under 37 CFR 1.113, or
 2. a Notice of Allowance under 37 CFR 1.311,
- whichever occurs first.

Also submitted herewith is:

- ☐ a certification as specified in 37 CFR 1.97(e);

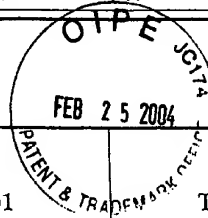
OR

- ☐ the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
OKI.227

In Re Application Of: Norio HIRASHITA



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MAR 03 2004

Serial No. NEW	Filing Date APRIL 5, 2001	Examiner TO BE ASSIGNED	Group Art Unit TO BE ASSIGNED
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Title: A STRUCTURE OF A FIELD EFFECT TRANSISTOR HAVING A METALLIC SILICIDE AND
MANUFACTURING METHOD THEREOF

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☐ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. _____ as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of _____
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I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. _____) on _____
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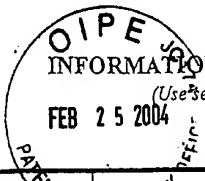
Dated: APRIL 5, 2001

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RESTON, VA 20191

TEL. NO. (703) 715-0870

CC:



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

FEB 25 2004

Docket Number (Optional)

OKI.227

Application Number

NEW

Applicant(s)

Norio HIRASHITA et al.

Filing Date

APRIL 5, 2001

Group Art Unit

TO BE ASSIGNED

*EXAMINER
INITIAL

TRADEMARK

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

A

Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication Engineers C-II Vol. J81-C-II No. 3, pp. 313-319, August 1998.

B

Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365.

C

Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.